

# 2SC1929

## Silicon NPN Planar Type

AF Output for Direct Main Operation TV

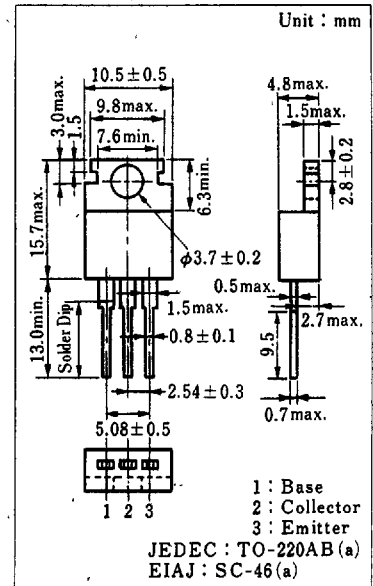
### ■ Features

- High collector-emitter voltage ( $V_{CE0}$ )
- Large collector power dissipation ( $P_C$ )

### ■ Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Collector-base voltage	$V_{CBO}$	300	V
Collector-emitter voltage	$V_{CEO}$	300	V
Emitter-base voltage	$V_{EBO}$	6	V
Peak collector current	$I_{CP}$	1	A
Collector current	$I_C$	0.4	A
Collector power dissipation ( $T_c=25^\circ\text{C}$ )	$P_C$	25	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

### ■ Package Dimensions



### ■ Electrical Characteristics ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=300\text{V}, I_E=0$			10	$\mu\text{A}$
Collector-emitter voltage	$V_{CEO}$	$I_C=10\text{mA}, I_B=0$	300			V
Emitter-base voltage	$V_{EBO}$	$I_E=5\text{mA}, I_C=0$	6			V
DC current gain	$h_{FE1}^*$	$V_{CE}=5\text{V}, I_C=0.1\text{A}$	35		330	
	$h_{FE2}$	$V_{CE}=5\text{V}, I_C=0.3\text{A}$	30			
Base-emitter voltage	$V_{BE}$	$V_{CE}=5\text{V}, I_C=0.1\text{A}$			1.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			2	V
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_C=0.1\text{A}, f=200\text{MHz}$		80		MHz

### \* $h_{FE1}$ Classifications

Class	S	R	Q	P
$h_{FE1}$	35~70	60~120	100~200	165~330

